

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least an inert gas;

providing the semiconductor film with a metal containing material; and

crystallizing the semiconductor film by heating after providing the metal containing material.

2. (Original) A method according to claim 1, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

3. (Original) A method according to claim 1, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In Sn, Pb, P, As, and Sb.

4. (Currently Amended) A method according to claim 1, further comprising ~~intercorporating~~ incorporating the semiconductor film into an electronic device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

5. (Original) A method according to claim 1, wherein the inert gas is argon.

6. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least an inert gas;

providing the semiconductor film with a metal containing material; and

crystallizing the semiconductor film by heating after providing the metal containing material; and

performing laser annealing to the semiconductor film after crystallizing the semiconductor film.

7. (Original) A method according to claim 6, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

8. (Original) A method according to claim 6, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As, and Sb.

9. (Currently Amended) A method according to claim 6, further comprising ~~interoperating~~ incorporating the semiconductor film into an electronic device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

10. (Original) A method according to claim 6, wherein the inert gas is argon.

11. (Original) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least nitrogen;

providing the semiconductor film with a metal containing material; and
crystallizing the semiconductor film by heating after providing the metal containing material.

12. (Original) A method according to claim 11, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

13. (Original) A method according to claim 11, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As, and Sb.

14. (Currently Amended) A method according to claim 11, further comprising ~~intercorporating~~ incorporating the semiconductor film into an electronic device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

15. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least nitrogen;
providing the semiconductor film with a metal containing material; and
crystallizing the semiconductor film by heating after providing the metal containing material; and
performing laser annealing to the semiconductor film after crystallizing the semiconductor film.

16. (Original) A method according to claim 15, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

17. (Original) A method according to claim 15, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As, and Sb.

18. (Currently Amended) A method according to claim 15, further comprising ~~intercorporating~~ incorporating the semiconductor film into an electronic device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

19. (Original) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least ammonia;

providing the semiconductor film with a metal containing material; and

crystallizing the semiconductor film by heating after providing the metal containing material.

20. (Original) A method according to claim 19, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

21. (Original) A method according to claim 19, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As, and Sb.

22. (Currently Amended) A method according to claim 19, further comprising ~~intercorporating~~ incorporating the semiconductor film into an electronic device selected

from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

23. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

exposing a semiconductor film to a plasma of a gas comprising at least ammonia;

providing the semiconductor film with a metal containing material; and

crystallizing the semiconductor film by heating after providing the metal containing material; and

performing laser annealing to the semiconductor film after crystallizing the semiconductor film.

24. (Original) A method according to claim 23, wherein the semiconductor film is exposed to the plasma by using a plasma CVD apparatus or a dry etching apparatus.

25. (Original) A method according to claim 23, wherein the metal containing material is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au, Al, In, Sn, Pb, P, As, and Sb.

26. (Currently Amended) A method according to claim 23, further comprising intercorporating incorporating the semiconductor film into an electronic device selected from the group consisting of a video camera, a digital camera, a projector, a head mounted display, a car navigation system, a car stereo, a personal computer, and a portable information terminal.

27. (New) A method of manufacturing a semiconductor device comprising the steps of:

 exposing a semiconductor film to a plasma of a gas selected from the group consisting of inert gas, nitrogen gas, and ammonia gas;

 providing the semiconductor film with a metal containing material; and

 crystallizing the semiconductor film by heating after providing the metal containing material.